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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE	
In re application of: Marwan H. Khater, et al.	Date: August 11, 2005
Serial Number: 10/709,222	Examiner: Joseph H. Nguyen
Filed: 4/22/04	Group Art Unit: 2815
Title: Structure and Method of Forming a Bipolar Transistor Having a Self-Aligned Raised Extrinsic Base Using Link-Up Region Formed From an Opening Therein	IBM Corporation D/18G, B/300, Zip 482 2070 Route 52 Hopewell Junction, NY 12533-6531

AMENDMENT UNDER RULE 312

Mail Stop: Issue Fee
Commissioner of Patents and Trademarks
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Responsive to the Notice of Allowance mailed July 1, 2005, please amend the application as follows: